Transmission electron microscopy study of a dental gallium alloy

A. E. GUNNÆS, A. OLSEN, H. HERØ*

Centre for Materials Research/Department of Physics, University of Oslo, Gaustadalleen 21,0371 Oslo, Norway * NIOM, Scandinavian institute of Dental Materials, P.B. 70, 1344 Haslum, Norway

Analytical transmission electron microscopy (TEM) studies of a dental gallium alloy have been carried out. This commercial Ga alloy was made by triturating a Ag-Sn-Cu-rich alloy powder with a liquid Ga alloy containing Ga, In and Sn. Ga alloys are of increasing interest as an alternative to amalgam. The dental material studied in the present work was found to be a composite consisting of remaining, undissolved particles from the Ag-based alloy powder in a matrix of reaction products with the liquid Ga alloy. The phases in the matrix and the remaining Ag-based alloy particles have been identified by electron diffraction, high resolution electron microscopy and energy dispersive X-ray spectroscopy. The following phases were identified: orthorhombic Ag₃Sn, cubic γ -Cu₉Ga₄, cubic Ag₉ln₄, tetragonal β -Sn and hexagonal Ag₂Ga. In addition to these well-known phases Ga-rich regions of Cu-Ga were observed consisting of an intergrowth of the tetragonal CuGa₂ and one of the cubic γ -Cu₉Ga₄ phases.

1. Introduction

Gallium alloys as a filling material and a replacement for amalgam was suggested for the first time by Puttkammer in 1928 [1]. Smith and Caul in 1956 [2] were the first to produce Ga alloys for dental purposes. In recent years the interest in Ga alloys for this application has increased because of the risk of environmental pollution from amalgam and the controversy about possible toxic effects of Hg in amalgam fillings [3].

In Japan a commercial Ga alloy (Gallium Alloy GF, Tokuriki Honton, Japan) has been on the market for some time. This alloy has also been approved by the health authorities of Japan. The composition of the Ag-based spherical alloy powder of this product is similar to that of an ordinary high Cu alloy for amal- $\frac{1}{2}$ $\frac{1}{2}$ $\frac{1}{2}$ is contained as much as $\frac{1}{2}$ as $\frac{1}{2}$ $\frac{1}{2}$ $\frac{1}{2}$ $\frac{1}{2}$ $A \cdot 1 = A \cdot 1 = A \cdot 1 = A \cdot 1 = A \cdot 1 = A$ A liquid Ga alloy is to be mixed with this alloy powder
in the same way as for amalgam.

Ga has a melting point as low as $29.8 \degree C$ [4]. When $\frac{1}{2}$ is allowed with 19 wt $\frac{1}{2}$ is and 16 with $\frac{1}{2}$ in a melting point is an initial point in the below 10°C. An initial point in the second term melting point is reduced to below 10° C. An initially plastic material is formed by mixing this liquid with plastic material is formed by mixing this negate with int a provider. Each a margant it can be condensed into a prepared cavity where it then sets to a solid. The handling characteristics are reported to be inferior to that of amalgam [5], but can be overcome by special techniques and equipment. G_{eff} and other Ga allows have been founded been founded been founded been founded between G_{eff}

Ua Anoy Or and other Oa anoys have been found to have similar mechanical properties to that of leading high copper amalgams [6]. The corrosion properties of Ga alloys as tested in vitro, however, have been questioned $[7]$. Furthermore, Okabe *et al.* $[8]$ and

Jorgensen et al. [9], have reported values for setting expansion of the Ga Alloy GF that are clearly above the maximum level accepted in IS0 1559 "Dental alloys for amalgams" [10]. This effect has not been reported for other Ga alloys. The reason for this anomalous behaviour of Gallium Alloy GF is unknown.

These properties of Ga alloys must be reflected in their structures. Hence, optimization of their properties will benefit from an adequate knowledge of the structures of the alloys. Okabe et al. [6] and Herø et al. $[11]$ found, by X-ray diffraction and scanning electron microscopy (SEM) studies, Ga alloy GF to consist of unconsumed spherical particles of the alloy powder embedded in a matrix consisting of Ag_9In_4 , $Ag₂Ga$ and β -Sn grains. A reaction layer of CuGa₂ $\frac{1}{G}$ cu, Ga, was surrounded the pre-allow particles. The pre-allow particles. $\frac{1}{4}$ summatric of Ga allows made on the basis of Ga allows $\frac{1}{4}$ and $\frac{1}{4}$ allows of Ga allows of Ga allows of Ga allows $\frac{1}{4}$ A similar structure of Ga alloys made on the basis of spherical alloys with high Cu content intended for amalgam has been observed by Okabe et al. [8].

A Ag-based alloy powder intended for amalgam has been reported, on the basis of X-ray diffraction, to α consisted, on the basis of Λ -ray dimachon, α $\frac{1}{2}$ have, $\frac{1}{2}$ and orthorhomore $\frac{1}{2}$ and $\frac{1}{2}$ have, $\frac{1}{2}$ have, $\frac{1}{2}$ ilarly, Herø et al. $[11]$ have, for the alloy powder made for gallium alloy GF, also observed indications of a hexagonal Ag₃Sn phase by using X-ray diffraction.

The aim of the present work was to characterize the microstructure of the gallium alloy GF further by transmission electron microscopy. The main purpose of this TEM study was to identify the phases present in the alloy by using selected area electron diffraction, high resolution electron microscopy and energy dispersive X-ray spectroscopy. This Ga alloy contains as

many as seven different elements, and many phases and a complex microstructure were expected to be found. Because the same dental Ga alloy has previously been studied by Herø et al. [11] using X-ray powder diffraction, a comparison of the results found in the present TEM investigation and the X-ray study will be made.

2. Experimental procedures

2.1. Materials

The dental Ga alloy GF was made by triturating a Ag-based alloy powder with a liquid Ga alloy. The powder to liquid ratio was 1:0.65 by weight. The compositions of the applied alloy powder and the liquid Ga alloy for the commercial Ga alloy GF according to the manufacturer are given in Table I. The dental material is the same as designated Ag-based GF powder in the paper by Herø et al. $[11]$ and more details about the material preparation can be found in their paper.

2.2. Sample preparation for TEM

Mechanically polished samples with thickness of the order of 50 μ m and diameters less than 3 mm were the starting materials for the TEM study. The samples were first mechanically thinned by dimpling with a Gatan dimple grinder model 656. During the dimpling procedure 15 and 1 um diamond paste and polishing wheels were used. The dimpling was stopped when a tiny hole was seen in the specimen. Because the specimens were less than 3 mm in diameter (which is the size of the TEM specimen holder) they were glued to Cu grids. The central part of the Cu grids was removed before the samples were glued, so the Cu grids would not interfere during the TEM study. After the dimpling procedure the specimens were thinned with Ar ions at 4 kV for about 2 h in a Gatan Dual ion-mill 600. The gun currents were 0.5 mA per gun and the specimen surface was oriented 12" relative to the incident ion beams.

2.3. Analytical electron microscopy

 $T_1 = 1 + 1$ G allows was examined at 200 kV in a JEOL 2000 FX transmission design microscope a JEOL 2000 FX transmission electron microscope equipped with a Tracor Northern X-ray detector and α SCAND Matrix α -ray and α -ray and α -ray and α -ray α -ray and a SCARD NORDAA A-lay analysed. In order to characterize the microstructure of the dental Ga alloy, a combination of bright field (BF), dark field (DF), high resolution electron microscopy (HREM), selected

TABLE I Material compositions according to the Ga alloy GF $IMBLEIN$

Sn Element Αg 25.7 Weight % 50 Liquid GA alloy	Cu 15	Pd q	Zn 0.3
Ga Element	In	Sn	
65 Weight %	19	16	

TABLE II $K_{.85}$ -factors (with their accuracies in parenthesis) at 200 kV used in the Cliff-Lorimer equation. (Equation 1)

Element	$K_{\rm{isi}}$	
Cu	0.59(0.02)	
Zn	0.60(0.02)	
Ga	0.61(0.02)	
Pd	1.35(0.03)	
Αg	1.50(0.03)	
In	1.77(0.03)	
Sn	2.06(0.03)	

area electron diffraction (SAD) and energy dispersive X-ray spectroscopy (EDS) was used. From the X-ray intensity data of the EDS analyses, the concentration ratios between the elements in each crystalline phase ere found by using the Cliff-Lorimer equation [13]:

$$
\frac{C_1}{C_2} = \frac{K_{1\text{Si}} * I_1}{K_{2\text{Si}} * I_2} \tag{1}
$$

 C_1 and C_2 are the concentrations of the elements 1 and 2, respectively, given in at %. K_{1Si} and K_{2Si} are the K-factors of the elements relative to Si. I_1 and I_2 are the intensities of the X-ray peaks from element 1 and 2 in the EDS spectrum. The K_{isi} -factors may vary from instrument to instrument depending on the type of detector and specimen surroundings. The K_{iS} factors are also depending on the accelerating voltage, but are independent of the specimen thickness and the composition as long as the thin film approximation is valid. The K_{i5i} -factors used in the present investigation were taken from Olsen [14], where experimental and calculated K_{iS} -factors for 200 kV are given as a function of the atomic number Z of element i . In Table II the K_{iS} -factors are given with their standard deviations is parentheses.

3. Results and discussion

The dental Ga alloy GF was found to be a composite consisting of undissolved particles from the Ag-based alloy powder surrounded by a matrix of reaction products. The phases in the matrix and the remaining parts of the Ag-based alloy particles have been identified and are described in the following.

3.1. The $Ag₃Sn$ phase

The remaining, undissolved Ag-based alloy powder particles were found to consist of Ag_3Sn grains $\sum_{i=1}^{n}$ is $\sum_{i=1}^{n}$ containing particles were reduced to contain of $\sum_{i=1}^{n}$ (Fig. ia). The case of the containing particles were σ_{0} served. In Fig. 1b a typical EDS spectrum from the Ag₃Sn phase is presented. The Ag L_{B2} (3.347 keV) and Sn L_{α} (3.443 keV) peaks was difficult to distinguish because the energy difference is at the limit of the energy resolution (145 eV at 5.894 keV) of the applied energy dispersive spectrometer. This made it difficult to determine the composition ratio between the two elements Ag and Sn by use of the Cliff-Lorimer equation (Equation 1). $\sum_{i=1}^{n}$ in Fig. la the diameter of the grains are in Fig. 1.

 t_{N} as shown in Fig. 1a the diameter of the grains are in

Figure 1 (a) BF image showing Ag₃Sn grains, and (b) corresponding EDS spectrum showing the nearly overlapping Ag L₆₁ and Sn L₂ peaks.

Figure 2 SAD patterns of the Ag₃Sn phase. (a) Experimental [100] projection with weak reflections indicated by arrow; (b) experimental [0 1 1] projection; and (c) corresponding schematic drawing.

however, also seen in the particles. In Fig. la some "dots" can be seen in the image. The "dots" have been examined by use of EDS and SAD. According to the SAD analyses the "dots" do not contribute to any extra reflections in the diffraction patterns from $A \in \mathbb{C}$ are not particles, $A \in \mathbb{C}$ are not particles, but $A \in \mathbb{C}$ $\frac{1}{2}$ rather behaviour the cause are not part T_1 can be seen by the Section comp.
 $T_1 = 24D$ patherns (Fig. 2) the Ag,Sn phase S_1

 $\frac{1}{2}$ corresponding to an orthorhomometer with space $\frac{1}{2}$ correspond to an ormormomore structure with space group \mathbf{r} minimized are consistent with the cendimensions $a = 0.5968$ nm, $b = 0.47802$ nm and $c = 0.51843$ nm as published by Fairhurst and Cohen $\epsilon = 0.51645$ lines published by Family and Conchete $\epsilon = 1.37$. In $\epsilon = 1.27$. In ϵ $\frac{1}{2}$ cased on single-erysian A-ray dimidentification [12]. In Fig. 2a the high symmetry projection $[1\ 0\ 0]$ is shown. Two types of reflections can be recognized. On the positive film one type of reflections can easily be seen. The other type is weak and more difficult to see (indicated by arrow). In the $[011]$ SAD pattern (Fig. 2b) three type of reflections can be recognized. The strongest reflections can easily be seen. In addition there are weak and even weaker reflections in this projection as indicated in the schematic drarwing in Fig. 2c. These very weak reflections are difficult to see on the positive film and may be even more di!Rcult to on the positive finite and may be even i

recognize by X-ray powder diffraction.
The cell dimensions found in the present investiga t_{tot} from the corresponding values of the corresponding values of the orthomeomorphoment and corresponding values of the σ thorhombic Ag_3Sn phase as given by Herø et al. [11]. They found that the dental material consists of a Ag-Sn rich phase which most likely is hexagonal or possibly orthorhombic. By use of X-ray powder diffraction the cell dimensions of the orthorhombic $Ag₃Sn$ phase were found to be consistent with $a = 0.4801$ nm, $b = 0.4780$ nm and $c = 0.3048$ nm. This c -axis is approximately half the a -axis value as found in the present investigation. The discrepancy may be due to the very weak reflections in the electron diffraction patterns giving the doubling of the 0.3048 nm axis. The hexagonal ζ -Ag₃Sn phase also reported by Herø et al. $[11]$ based on X-ray powder diffraction for the same dental material was not observed in the present TEM study.

Figure 3 (a) BF image showing region of the Cu₉Ga₄ phase with (b) the corresponding EDS spectrum.

3.2. Cu-Ga phases

In the zones between the remaining powder particles and the matrix two types of Cu-Ga regions were found by analytical TEM: Cu-rich and Ga-rich.

The Cu-rich phase was identified to be consistent with one of the cubic γ -Cu₉Ga₄ phases with space group P43m and cell dimension $a = 0.8747$ nm as given by Stokhuyzen et al. [15]. The $Cu₉Ga₄$ phase does not seem to have a characteristic grain structure (Fig. 3a). The typical size of the regions is of the order of 1.5 μ m, but some grains may be larger than 1.5 μ m. The EDS spectrum in Fig. 3b was recorded from the area shown in Fig. 3a. By using the Cliff-Lorimer equation (Equation 1) the composition ratio between Cu and Ga was found to be approximately 2. According to Massalski et al. [16] the γ_1 -Cu₉Ga₄ phase has a composition range of 30-35 at % Ga. Thus, the experimental composition value of the present dental material is in good agreement with this. According to Herø et al. $[11]$ the X-ray diffraction indicates a minor fraction of the cubic $Cu₉Ga₄$. In Fig. 4a, b and c three different SAD patterns are shown: the $[0\ 0\ 1]$, $[1\ 1\ \overline{1}]$ and $\lceil 1 \rceil \rceil$ projections, respectively.

The Ga-rich regions have a composition about 60 at % Ga as found by EDS analyses. Fig. 5 shows three different SAD patterns taken of this Ga-rich regions. These diffraction patterns have some similarities with the SAD patterns from the $Cu₉Ga₄$ phase shown in Fig. 4. There are, however, some very important differences both in the position and the intensity of the reflections. In the SAD patterns shown in Fig. 5 there are large differences in intensity between the strong and weak reflections whereas the SAD patterns shown in Fig. 4 there is much less difference in intensity between the strong and weak reflections.

Fig. 6 shows three other SAD patterns from the Ga-rich Cu-Ga regions. In these patterns the shortest distance between the reflections corresponds to a d-value of 1.75 nm. It is also to be noticed that the distance between the strong reflections in all the SAD patterns from this phase is divided into three by weak reflections. This could indicate that the structure of the Ga-rich Cu-Ga regions has a unit cell with dimensions three times a basic cell.

BF, DF and HREM show, however, that these Ga-rich regions are intergrowths of two phases. In Fig. 7a the BF image shows grains of the Ga-rich Cu-Ga regions. The grains have diameters of the order of $1 \mu m$. The contrast is a modulated type with the modulation vector normal to the c-axis. One should notice that the contrast is different in different grains and depends on the crystal orientation. The contrast is also different from the image contrast of the $Cu₉Ga₄$ phase shown in Fig. 3a.

In the Ga-rich part of the phase diagram relatively few phases have been reported in the literature. The q-phase reported by Weibke [17] has a composition near 56 at % Ga and exists below 249 "C. This phase was subsequently reported by Zintl and Treusch [18] to be tetragonal with cell dimensions $a = 0.2836$ nm, $c = 0.5847$ nm and space group P4mm. They observed that this phase was homogeneous at 58 at % Ga, but according to them the unit cell contains three atoms. Therefore they suggested that the composition of this phase should be $CuGa₂$ and the atomic positions Cu $(1b) \frac{1}{2} \frac{1}{2}$ 0.27, Ga $(1b) \frac{1}{2} \frac{1}{2}$ 0.70, Ga $(1a)$ 0 0 0. Subsequently Betterton and Hume-Rothery [19] found that this phase does not contain 56 at $\%$ Ga as reported by Weibke [171, but corresponds almost exactly to the composition $CuGa₂$. They called this phase the θ -phase. The cell dimensions of this phase were later determined by El-Boragy and Schubert [20] to be $a = 0.2830$ nm, $c = 0.5839$ nm. However, they concluded that the structure has the $FeSi₂$ -type and the space group P4/mmm. According to them the atomic positions are: Cu(1a) 000, Ga(2h) $\frac{1}{2}$ $\frac{1}{2}$ 0.295. In the phase diagram published by Massalski et al. [16], the φ -phase has been called the ε -phase.

An EDS spectrum of this Ga-rich region is shown in Fig. 7b. By using the Cliff-Lorimer equation

Figure 4 SAD patterns of \cdot

(Fig.) the composition $\mathcal{L}(\mathcal{L})$ the composition was found to be approximated to b Equation 1 ine composition was found to be approx imately 60 at % Ga. In the Cu-Ga phase diagram [16] this would be at the left-hand side of the ε phase. A comparison of the results in the present investigation

with the literature shows that the problems that the problems that the problems of the problems of the problems with the interature shows that the present Ga-Hen regions are intergrowths of two Cu-Ga phases, the tetragonal $CuGa₂$ and one of the cubic γ -Cu₉Ga₄ phases. A more detailed analysis of these regions will be published elsewhere.

Figure 6 SAD patterns taken the Ga-rich Cu-Ga regions showing dense rows of reflections.

According to Herø et al. [11] the Ga content of the Ga-rich phase θ -Cu(Pd) Ga₂ is 77.7 at %. In addition they also reported 7.9 at % Pd in this phase. Pd was, however, not detected in the present work.

3.3. The Ag₉In₄ phase

The matrix in the dental Ga alloy was found to consist mainly of the Ag_9In_4 phase. The regions with the Ag₉In₄ phase are found to consist of large grains containing subgrains. The exact size of the grains was not determined. The SAD patterns correspond to a cubic structure with space group P43m and cell dimensions consistent with $a = 0.9922$ nm as published

Figure 7 (a) BF image showing grains of the Ga-rich Cu-Ga phase and (b) corresponding EDS spectrum.

b

Figure 8 (a) HREM image of the Ag₉In₄ phase seen in the [1 1 1] orientation. (b) Corresponding SAD pattern; and (c) EDS spectrum showing the Ag $L_{\beta1}$ and In L_{α} peaks.

by Brandon et al. [21]. Fig. 8 shows a HREM image (a) and its corresponding SAD pattern (b). As may be seen from the HREM image the Ag_9In_4 phase seems to show similar modulated contrast features as the Ga-rich Cu-Ga regions. This feature is, however, not so characteristic as for the Ga-Cu case.

The EDS spectrum of the Ag_9In_4 phase (Fig. 8c) looks very similar to the EDS spectrum from the Ag,Sn phase (Fig. lb). As shown in Fig. 8c the Ag L_{61} (3.150 keV) and In L_{α} (3.286 keV) peaks overlap. Just as for the Ag,Sn phase this makes it difficult to determine the ratio between the two elements by use of the Cliff-Lorimer equation (Equation 1). The modulated contrast may be due to an intergrowth of Ag₉In₄ and Ag₃Sn. These two phases have very similar dimensions in the $[1 0 0]$ projections. The Ag₉In₄ is cubic with cell dimensions $a = 0.9922$ nm [21] and the periodicity along the (011) directions is 1.4032nm. The Ag,Sn phase is orthorhombic with cell dimensions $a = 0.5968$ nm, $b = 0.47802$ nm and $c = 0.51843$ nm [12]. The periodicity along the (011) directions is 0.7051 nm. The angle between

 $[011]$ and $[01\overline{1}]$ is 94.64°, whereas the corresponding angle in the Ag_9In_4 phase is 90°. Therefore in the [100] projections there is a simple relationship between the lattices of the two phases: Ag_3Sn $(011) \approx$ Ag₉In₄ $\frac{1}{2}$ (011). These two phases are also difficult to distinguish by EDS due to the following overlaps:

$$
Ag L_{\beta 2}(3.347 \text{ keV}) \approx \text{In } L_{\beta 1}(3.487 \text{ keV}) \approx \text{Sn } L_{\phi}(3.443 \text{ keV})
$$

In $L_{\beta 2}(3.713 \text{ keV}) \approx \text{Sn } L_{\beta 1}(3.662 \text{ keV})$

3.4. The Sn phase

Almost pure Sn was found to cover large areas: The Sn phase was found in contact with the Ag_9In_4 and sometimes the Ga-Cu phases. The Sn phase corresponds to the tetragonal β -structure published by Deshpande and Sirdeshmukh [22] with space group 14₁/amd and cell dimensions $a = 0.58318$ nm and $c = 0.31819$ nm. In Fig. 9a DF image taken of the Sn phase is shown. Some small particles in the Sn phase can be seen. The EDS spectra taken from these

Figure 9 (

Figure 10 (a) BF image; (b) SAD pattern; and (c) EDS spectrum taken from the Ag₂Ga phase.

particles show that they are Ag-rich, but no further analyses were carried out in order to determine more accurately the Ag content. The [10 0] SAD patterns of the Sn regions show diffuse streaks along the $\langle 100 \rangle$ directions (Fig. 9b). These streaks are not due to precipitates, but may be due to thermal vibrations of the Sn atoms. Such thermal diffuse streaks in SAD patterns from Sn are well known [23] and are due to an intersection between diffuse walls of scattered electrons and the Ewald sphere. Both the EDS spectrum (Fig. 9c) and the SAD pattern (Fig. 9b) with diffuse streaks are very characteristic of the Sn phase found in the present dental material.

3.5. The $Ag₂Ga phase$

A $Ag₂Ga$ phase was also observed in the matrix of the dental material. This phase was found to be consistent with a hexagonal structure with space group $\overline{P6}$ and cell dimensions $a = 0.77677$ nm and $c = 0.28778$ nm as published by Stratton and Kitchingman [24]. In Fig. 10 a BF image (a) of the Ag_2Ga phase with its corresponding SAD pattern (b) is shown. The area in Fig. 10a consists of several small grains. Large amount of moiré patterns caused by overlapping grains can be of more patterns caused by overtapping grams can be $\frac{1}{10}$ for $\frac{1}{10}$ phase was recorded from the region shown show the Ag_2Ga phase was recorded from the region shown
in Fig. 10a.

3.6. The presence of Pd and Zn No indications of Pd or Zn were found in the EDS

The indications of Γ d of Γ were found in the ED. analyses. Pd has previously been found associated with Cu and Ga in this dental Ga alloy by use of EDS in SEM [11]. Pd should be seen in the present investigation if the Pd concentration is as high as 7.9 at $\%$ as reported by Herø et al. [11] for the Ga rich Cu-Ga phase. If the Pd and Zn are spread over a large volume (low concentration) it may be difficult to detect these elements by use of EDS. These elements may also be difficult to detect if they are concentrated along grain
boundaries. In this latter case they may be detected in

a SEM, but not in TEM due to the larger analysed volumes in SEM.

4. Conclusions

The present work has shown that the investigated dental material consists of remaining undissolved particles from the Ag-based alloy powder in a matrix of reaction products with the liquid Ga alloy. Between the particles and the matrix reaction zones were found. The particles consist of orthorhombic Ag_3Sn . In the matrix the following phases were found: cubic Ag₉In₄, tetragonal β -Sn and hexagonal Ag₂Ga. The reaction zones were found to consist of two types: the cubic γ -Cu₉Ga₄ and Ga-rich Cu-Ga regions which are intergrowths of the tetragonal $CuGa₂$ and one of the γ -Cu₉Ga₄ phases. The crystalline phases identified by use of TEM in the present work, their space group and cell dimensions are given in Table III. The space groups and cell dimensions can be found in Villars and Calvert [25].

As mentioned earlier, X-ray diffraction has previously been used to identify the phases in this dental Ga alloy. Some disagreements between the TEM and X-ray results have been found. In Table VI the phases identified by use of X-ray diffraction is summarized [11]. The major differences between the results from t_{H} -ray diffraction study and the present Temperature Tempe inc λ -iay annaction stuay.

TABLE II I I I I I Space group and cell dimensions of the identified \mathcal{L} **HABLE** III Space group and cell dimensions of the

Phase	Space group	Cell dimensions (nm)			
		a	b	c	
$Ag_{3}Sn$	Pmmn	0.5968	0.47802	0.51843	
Ag, Ga	Põ.	0.77677		0.28778	
Cu ₉ Ga ₄	$P\overline{4}3m$	0.8747			
Ga-Cu intergrowth					
Ag_9In_4	$P\bar{4}3m$	0.9922			
Sn	14 , $/$ amd	0.58318		0.31819	

TABLE IV Space group and cell dimensions of the identified phases in the dental Ga alloy as found by Herø et al. [11]

Phase	Space group	Cell dimensions (nm)			
		α	b	с	
ζ -Ag ₃ Sn	$P6_2/mmc$	0.2970		0.4774	
ζ' -Ag ₃ Sn	Pmmn	0.4801	0.4780	0.3048	
ζ -Ag ₆ Ga ₃	P3	0.7736		0.2872	
θ -Cu(Pd) Ga,	P4/mmm	0.2818		0.5796	
γ -Ag ₉ In ₄	P43m	0.9830			
β -Sn	14 , $/$ amd	0.5799		0.3171	

According to Herø et al. [11] the particles consist of both an orthorhombic (ζ') and a hexagonal (ζ) phase of Ag₃Sn, whereas only the orthorhombic (ϵ) phase was found in the TEM study. There are also differences in composition and cell dimensions of the orthorhombic (ζ) and (ε) phases. The ζ -phase has cell dimensions: $a = 0.4801$ nm, $b = 0.4780$ nm and $c = 0.3048$ nm whereas the ε -phase has: $a = 0.5968$ nm, $b =$ 0.47802 nm and $c = 0.51843$ nm. Two axes are approximately equal in the two structures, but the third axis is doubled in ε -phase compared to the ζ -phase.

Another difference between the results of the two investigations concerns the presence of the Ga-rich Cu-Ga regions. According to Herø et al. $[11]$ the reaction zones around the particles consist of a tetragonal θ -Cu(Pd)Ga₂ phase and a cubic Cu₉Ga₄ phase. The cubic phase was also found in the present TEM work, but instead of the tetragonal θ -Cu(Pd)Ga₂ phase the Ga-rich Cu-Ga regions consist of an intergrowth between the tetragonal $CuGa₂$ and one of the cubic γ -Cu₉Ga₄ phases. No indication of Pd was found in these regions.

According to Herø et al. [11] the β -Sn phase appears as white particles in matrix and contains a substantial amount of Ga, In and Ag. The maximum solubility of Ga and In in Sn according to the binary phase diagrams was in agreement with their experimental observations, whereas the measured content of Ag and Cu in β -Sn was higher than expected from the binary phase diagrams. According to Herø et al. [11] this discrepancy could "be due to either small precipitates not visible by SEM or interference from surrates not visible by SEM of interference from surpure Spin was found to cover the cover design to cover and the cover design of the cover of pure Sn was found to cover large areas, but some small particles in the β-Sn phase were also seen. $A = \frac{1}{2}$ and $A = EDE = \frac{1}{2}$ and $A = EDE$ \sum_{1}^{1}

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